

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"6812547".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:45
S2	327	gettering near4 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:00
S3	2	"6150239".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 08:24
S4	2332015	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 08:28
S5	44182	diffusion adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/09 08:28
S6	6	S2 and S4 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:13
S7	11949	device adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:13
S8	2335534	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:13

S9	44252	diffusion adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:13
S10	1961	collection adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:14
S11	2	S7 and S8 and S9 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:11
S12	199	S7 and S8 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:16
S13	327	gettering near4 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:34
S14	2	"6673400".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 13:34
S15	2	("4149301" "5371699").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/16 14:25
S16	386	hydrogen adj getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 14:26
S17	138	S8 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 14:26
S18	10	("5760433").URPN.	USPAT	OR	ON	2005/12/16 14:33

S19	2	"6673400".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 10:56
S20	398	gettering adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:02
S21	320	heat adj dissipation adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:03
S22	12025	device adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:03
S23	2342095	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:03
S24	0	S20 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:04
S25	379	S20 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:18
S26	700	ion adj (cut or cutting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:18

S27	79	S23 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:37
S28	2	"5494835".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 11:37
S29	680	smart adj cut	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:16
S30	2342095	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:16
S31	327	gettering near4 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:16
S32	387	hydrogen adj getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:16
S33	47	S32 and S30 and S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:20
S34	663	S29 and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:20

S35	0	S34 and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:20
S36	5	S34 and S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:48
S37	5215	(diffusing or diffusion) near2 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:49
S38	13	S29 and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:10
S39	12025	device adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:12
S40	1969	collection adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:12
S41	10	S39 and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:13
S42	364	hydrogen adj (implanting or implantation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:13

S43	5188	bower.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 06:16
S44	700	ion adj (cut or cutting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 06:16
S45	10	S44 and S43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 06:34
S46	2	"6323109".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 06:34
S47	11	("4837172" "5374564" "5476813" "5633174" "5710057" "5714395" "5854123" "5877070" "5882987" "5953622" "6083324").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/30 07:27
S48	4	("6323109").URPN.	USPAT	OR	ON	2005/12/30 07:20
S49	133	hydrogen adj collection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 07:29
S50	387	hydrogen adj getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 07:43
S51	2	"6387829".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:01

S52	2	"6346459".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/30 08:02
S53	25	((("5374564") or ("5494835") or ("5877070") or ("6150239") or ("6162705") or ("6346458") or ("6352909") or ("6033974") or ("6100166") or ("5882987") or ("5926720") or ("5966620") or ("5710057") or ("6027988") or ("6048411") or ("6054370") or ("6140210") or ("6159824") or ("6225190") or ("6225192") or ("6069059") or ("6191007") or ("6245249") or ("6290804") or ("6426831"))).PN.	USPAT	OR	OFF	2005/12/30 08:51
S54	6	((("6150239") or ("6069059") or ("6124185"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/30 08:52
S55	23471	copper adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 13:17
S56	1624395	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 13:17
S57	17	rf adj shield adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:41
S58	22	(rf adj shield or reflective adj shield) adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 13:19

S59	328	gettering near4 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:07
S60	798	(getter or gettering) near2 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:08
S61	1635223	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:08
S62	236	S60 and S61	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:13
S63	12202	device adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:13
S64	17	S63 and S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:39
S65	2	"5362667".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:52
S66	2	"5882990".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 07:57

S67	2	"5362667".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:05
S68	42843	delamination or delaminating or delaminated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:06
S69	328	gettering near4 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:06
S70	11	S69 and S68	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:08
S71	1635223	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:08
S72	6596	S68 and S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:09
S73	2360748	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:09
S74	5572	S73 and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:09

S76	23548	gettering or getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:09
S77	112	S74 and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:10
S78	191	S68 and S73 and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:10
S79	2360748	substrate or wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:45
S80	23548	gettering or getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:45
S81	11098	S80 and S79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:46
S82	2181069	transfer or transferring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:46
S83	2211	S81 and S82	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:46

S84	1123	(getter or getting or gettered) near4 hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:46
S85	115	S83 and S84	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:48
S86	695265	bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:48
S87	130729	S82 and S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:48
S88	759	S79 and S80 and S87	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:48
S89	42	S84 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:48
S90	8	("5371037" "5374564" "5458755" "5726464" "5811348" "5856229" "5966620" "6107213").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/01 13:58
S91	2	"6054370".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:58
S92	10	("5238875" "5374564" "5494835" "5559043" "5714395" "5863832" "5877070" "5882987" "5949108" "5953622").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/01 15:03

S93	3699	Simox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:04
S94	172	aspar.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:04
S95	11	S93 and S94	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:04
S96	1048	henley.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:04
S97	10	S93 and S96	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:07
S98	309	bruel.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:07
S99	15	S93 and S98	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 15:09
S10 0	2	"6020252".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 16:53

S10 1	695265	bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 16:53
S10 2	1609	S93 and S101	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 16:56
S10 3	1098845	hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 16:56
S10 4	645	S102 and S103	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 17:22
S10 5	17704	getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 17:23
S10 6	24034	getter or gettering or gettered	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 17:23
S10 7	115	S104 and S106	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 17:23
S10 8	433	hydrogen adj (getter or gettering)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:46

S10 9	695803	bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:00
S11 0	69	S108 and S109	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:03
S11 1	25496	planarizing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:03
S11 2	130	S109 near4 S111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:04
S11 3	12457	(wafer or substrate) adj bonding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:05
S11 4	3490	(wafer or substrate) adj transferring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 12:05
S11 5	3705	simox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:05
S11 6	537	plasma adj (injecting or injection)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 13:03

S11 7	1290	pulse adj heating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 13:03
S11 8	2577	ion adj (implanting or implantation) near3 plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 13:38
S11 9	911	ion adj (implanting or implantation) near1 plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 13:51
S12 0	155908	metal adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:09
S12 1	3070298	via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:09
S12 2	172	aspar.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:20
S12 3	8	S120 and S122	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:24
S12 4	1124	438/455.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:25

S12 5	129	S120 and S124 and S121	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:25
S12 6	1636244	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:41
S12 7	1269	rf adj shield	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:41
S12 8	235	S126 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:43
S12 9	60133	heat adj dissipation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:43
S13 0	323	heat adj dissipation adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:43
S13 1	134	S126 and S130	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/03 14:43